CLAIMS

What is claimed is:

1. A method comprising:

in a wafer processing environment, introducing a liquid via a carrier gas; and

separate from the liquid, introducing a first gas comprising ozone and a legacy amount of oxygen and a second gas comprising an effective amount of oxygen to modify a process operation.

2. The method of claim 1, wherein introducing the first gas and the second gas further comprises:

forming the first gas; and

after forming the first gas, combining the second gas and the first gas.

3. The method of claim 1, wherein introducing the first gas and the second gas comprises forming the first gas with the legacy amount of oxygen and the second gas.

4. The method of claim 1, wherein the wafer processing environment comprises an etching environment, and the effective amount of the second gas modifies the etch rate of an etch operation.

5. The method of claim 1, wherein the wafer processing environment comprises a film formation environment, and the effective amount of the second gas modifies the film formation.

6. A system comprising:

a chamber;

a liquid source coupled to the chamber;

a first gas source coupled to the chamber;

a second gas source coupled to the chamber;

a controller configured to control the introduction into the chamber of a liquid from the liquid source, a first gas comprising ozone and a legacy amount of oxygen from the first gas source, and a second gas comprising oxygen from the second gas source; and

a memory coupled to the controller comprising a machine-readable medium having a machine-readable program embodied therein for directing operation of the system, the machine-readable program comprising:

instructions for controlling the second gas source to introduce an effective amount of oxygen into the chamber to modify a process operation.

7. The system of claim 6, wherein the first gas and the second gas are introduced through a single line coupled between the first gas source, the second gas source, and the chamber.

8. The system of claim 7, wherein the first gas source and the second gas source comprise a single gas source.

9. A computer readable storage medium containing executable computer program instructions which when executed cause a digital processing system to perform a method comprising:

introducing a liquid via a carrier gas; and

separate from the liquid, introducing a first gas comprising ozone and a legacy amount of oxygen and a second gas comprising an effective amount of oxygen to modify a process operation.

10. The computer readable storage medium of claim 9, wherein introducing the first gas and the second gas further comprises:

forming the first gas; and

after forming the first gas, combining the second gas and the first gas.

11. The computer readable storage medium of claim 9, wherein introducing the first gas and the second gas comprises forming the first gas with the legacy amount of oxygen and the second gas.

12. The computer readable storage medium of claim 9, wherein the wafer processing environment comprises an etching environment, and the effective amount of the second gas modifies the etch rate of an etch operation.

13. The method of claim 9, wherein the wafer processing environment comprises a film formation environment, and the effective amount of the second gas modifies the film formation.